SEMICONDUCTOR
TOSHIBA
TECHNICAL DATA

TOSHIBA PHOTOCOUPLER
TLP250
GaAℓAs IRED & PHOTO-IC

(TLP250)

TRANSISTOR INVERTER
INVERTER FOR AIR CONDITIONOR
IGBT GATE DRIVE
POWER MOS FET GATE DRIVE

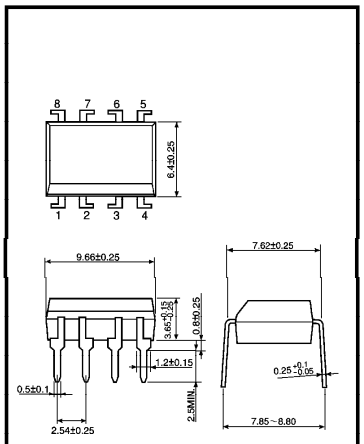
The Toshiba TLP250 consists of a GaAℓAs light emitting diode and a integrated photodetector.
This unit is 8-lead DIP package.
TLP250 is suitable for gate driving circuit of IGBT or power MOS FET.

- Input Threshold Current : I_F=5mA (Max.)
- Supply Current (I_{CC}) : 11mA (Max.)
- Supply Voltage (V_{CC}) : 10-35V
- Output Current (I_O) : ±0.5A (Min.)
- Switching Time (t_{pLH}/t_{pHL}) : 0.5μs (Max.)
- Isolation Voltage : 2500V_{rms} (Min.)
- UL Recognized : UL1577, File No.E67349
- Option (D4) type
  VDE Approved : DIN VDE0884 / 06.92, Certificate No.76823
  Maximum Operating Insulation Voltage : 630V_{PK}
  Highest Permissible Over Voltage : 4000V_{PK}

(Note) When a VDE0884 approved type is needed, please designate the "Option (D4)"

- Creepage Distance : 6.4mm (Min.)
  Clearance : 6.4mm (Min.)

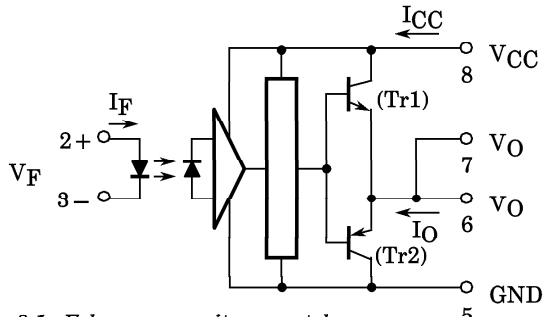
Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	11-10C4

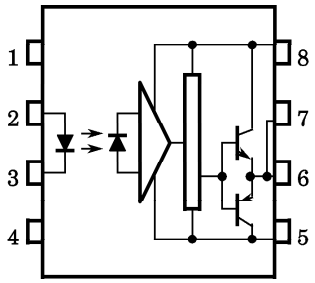
Weight : 0.54g

SCHMATIC



A 0.1μF bypass capcitor must be connected between pin 8 and 5 (See more 5).

PIN CONFIGURATION (TOP VIEW)



1 : N.C.
2 : ANODE
3 : CATHODE
4 : N.C.
5 : GND
6 : V_O (OUTPUT)
7 : V_O
8 : V_{CC}

TRUTH TABLE

		Tr1	Tr2
Input LED	ON	ON	OFF
	OFF	OFF	ON

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ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current		I_F	20	mA
	Forward Current Derating (Ta ≧ 70°C)		$\Delta I_F / \Delta Ta$	−0.36	mA / °C
	Peak Transient Forward Curent	(Note 1)	I_{FPT}	1	A
	Reverse Voltage		V_R	5	V
	Junction Temperature		(T_j)	125	°C
DETECTOR	"H" Peak Output Current (P_W ≦ 2.5μs, f ≦ 15kHZ)	(Note 2)	I_{OPH}	−1.5	A
	"L" Peak Output Current (P_W ≦ 2.5μs, f ≦ 15kHZ)	(Note 2)	I_{OPL}	+1.5	A
	Output Voltage	(Ta ≦ 70°C)	V_O	35	V
		(Ta = 85°C)		24	
	Supply Voltage	(Ta ≦ 70°C)	V_{CC}	35	V
		(Ta = 85°C)		24	
	Output Voltage Derating (Ta ≧ 70°C)		$\Delta V_O / \Delta Ta$	−0.73	V / °C
	Supply Voltage Derating (Ta ≧ 70°C)		$\Delta V_{CC} / \Delta Ta$	−0.73	V / °C
	Junction Temperature		(T_j)	125	°C
Operating Frequency		(Note 3)	f	25	kHz
Operating Temperature Range			T_{opr}	−20~70	°C
Storage Temperature Range			T_{stg}	−55~125	°C
Lead Solder Temperature (10s)			T_{sol}	260	°C
Isolation Voltage (AC, 1min., R.H. ≦ 60%, Ta = 25°C)		(Note 4)	BV_S	2500	Vrms

Note 1 : Pulse width P_W ≦ 1μs, 300pps

Note 2 : Exporenential Wavefom

Note 3 : Exporenential Wavefom, I_{OPH} ≦ −1.0A (≦ 2.5μs), I_{OPL} ≦ +1.0A (≦ 2.5μs)

Note 4 : Device considerd a two terminal device : pins 1,2,3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

Note 5 : A ceramic capacitor (0.1μF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching proparty. The total lead length between capacitor and coupler should not exceed 1cm.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.		UNIT
Input Current, ON	$I_{F(ON)}$	7	8	10		mA
Input Voltage, OFF	$V_{F(OFF)}$	0	—	0.8		V
Supply Voltage	V_{CC}	15	—	30	20	V
Peak Output Current	I_{OPH} / I_{OPL}	—	—	±0.5		A
Operating Temperature	T_{opr}	−20	25	70	85	°C

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ELECTRICAL CHARACTERISTICS (Ta = −20~70°C, Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION		MIN.	TYP.*	MAX.	UNIT
Input Forward Voltage		V_F	—	I_F=10mA, Ta=25°C			1.6	1.8	V
Temperature Coefficient of Forward Voltage		$\Delta V_F / \Delta Ta$	—	I_F=10mA		—	−2.0	—	mV / °C
Input Reverse Current		I_R	—	V_R=5V, Ta=25°C			—	10	μA
Input Capacitance		C_T	—	V=0, f=1MHz, Ta=25°C		—	45	250	pF
Output Current	"H" Level	I_{OPH}	3	V_{CC}=30V (*1)	I_F=10mA V_{8-6}=4V	−0.5	−1.5	—	A
	"L" Level	I_{OPL}	2		I_F=0 V_{6-5}=2.5V	0.5	2	—	
Output Voltage	"H" Level	V_{OH}	4	V_{CC1}=+15V, V_{EE1}=−15V R_L=200Ω, I_F=5mA		11	12.8	—	V
	"L" Level	V_{OL}	5	V_{CC1}=+15V, V_{EE1}=−15V R_L=200Ω, V_F=0.8V		—	−14.2	−12.5	
Supply Current	"H" Level	I_{CCH}	—	V_{CC}=30V, I_F=10mA Ta=25°C		—	7	—	mA
				V_{CC}=30V, I_F=10mA		—	—	11	
	"L" Level	I_{CCL}	—	V_{CC}=30V, I_F=0mA Ta=25°C		—	7.5	—	
				V_{CC}=30V, I_F=0mA		—	—	11	
Threshold Input Current	"Output L→H"	I_{FLH}	—	V_{CC1}=+15V, V_{EE1}=−15V R_L=200Ω, V_O>0V		—	1.2	5	mA
Threshold Input Voltage	"Output H→L"	V_{FHL}		V_{CC1}=+15V, V_{EE1}=−15V R_L=200Ω, V_O<0V		0.8	—	—	V
Supply Voltage		V_{CC}	—			10	—	35	V
Capacitance (Input-Output)		C_S	—	V_S=0, f=1MHz Ta=25°C		—	1.0	2.0	pF
Resistance (Input-Output)		R_S	—	V_S=500V, Ta=25°C R.H.≦60%		5×10^{10}	10^{14}	—	Ω

* All typical values are at Ta=25°C (*1) : Duration of I_O time≦50μs

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SWITCHING CHARACTERISTICS (Ta = −20~70°C, Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.*	MAX.	UNIT
Propagation Delay Time	L→H	t_{pLH}	6	I_F = 8mA V_{CC1} = +15V, V_{EE1} = −15V R_L = 200Ω	—	0.15	0.5	μs
	H→L	t_{pHL}			—	0.15	0.5	
Output Rise Time		t_r			—		—	
Output Fall Time		t_f			—		—	
Common Mode Transient Immunity at High Level Output		C_{MH}	7	V_{CM} = 600V, I_F = 8mA V_{CC} = 30V, Ta = 25°C	−5000	−	−	V / μs
Common Mode Transient Immunity at Low Level Output		C_{ML}	7	V_{CM} = 600V, I_F = 0mA V_{CC} = 30V, Ta = 25°C	5000	−	−	V / μs

* All typical values are at Ta = 25°C

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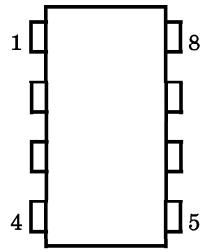
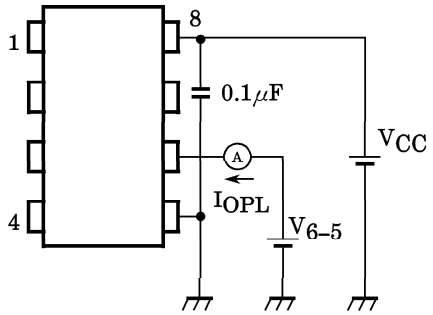
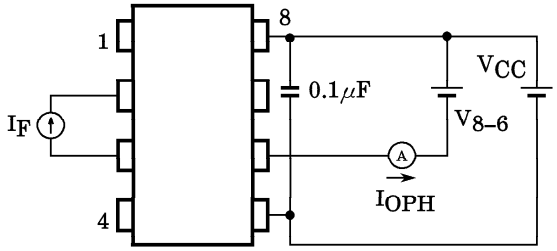
TEST CIRCUIT 1 :



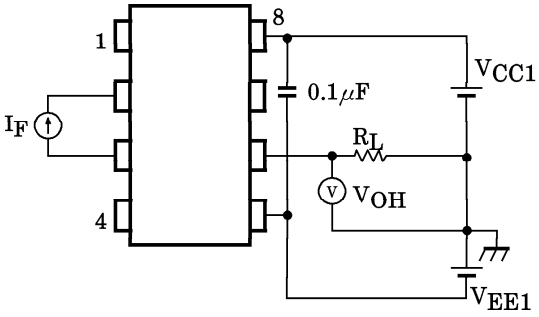
TEST CIRCUIT 2 : IOPL



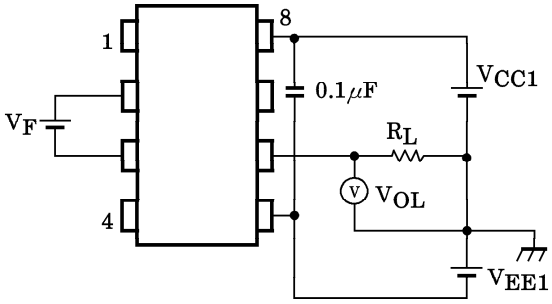
TEST CIRCUIT 3 : IOPH



TEST CIRCUIT 4 : VOH



TEST CIRCUIT 5 : V_{OL}



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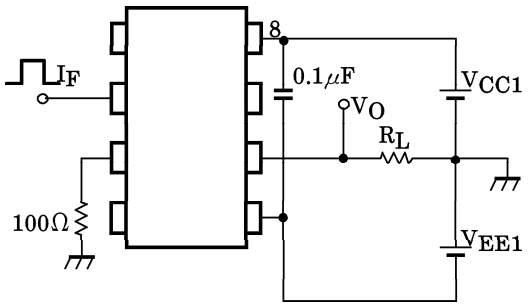
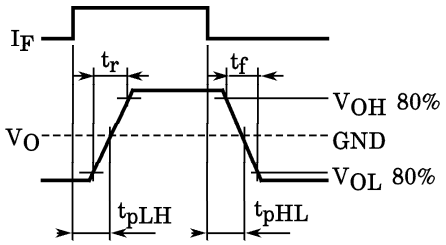
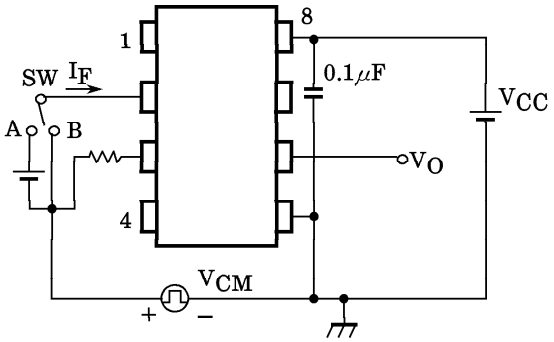
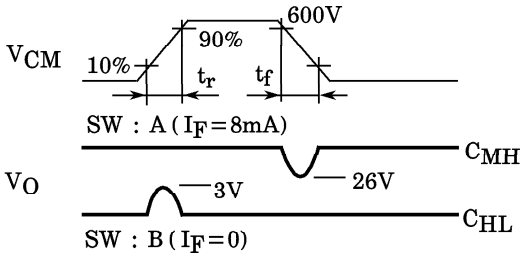
TEST CIRCUIT 6 : t_{pLH}, t_{pHL}, t_r, t_f





TEST CIRCUIT 7 : C_{MH}, C_{ML}





$$C_{ML} = \frac{480\,(V)}{t_r\,(\mu s)}$$

$$C_{MH} = \frac{480\,(V)}{t_f\,(\mu s)}$$

C_{ML} (C_{MH}) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

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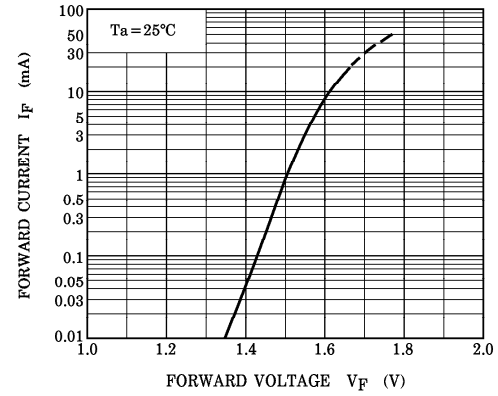
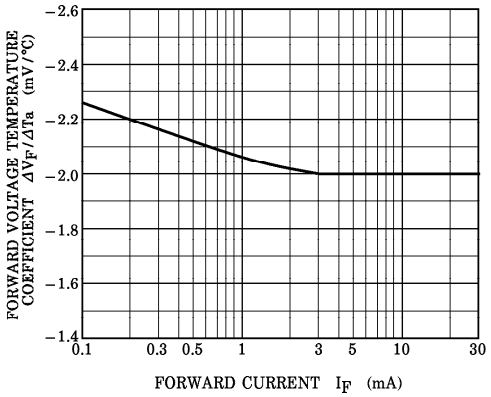
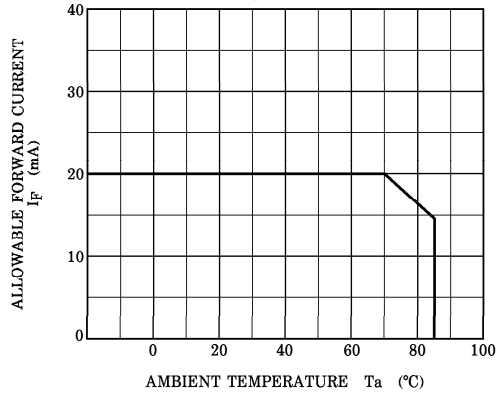
$I_F - V_F$



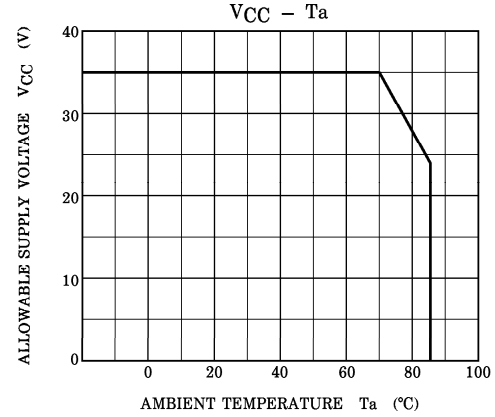
$\Delta V_F / \Delta Ta - I_F$



$I_F - Ta$



$V_{CC} - Ta$



$I_{OPH}, I_{OPL} - Ta$